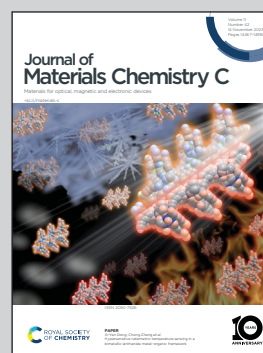


Research from the Laboratory for Information Materials and Electro-devices at Hanyang University, Seoul, Republic of Korea.

Tailoring thin film transistor performance through plasma reactant manipulation in indium oxynitride films

The different atomic layer deposition reaction mechanisms of two nitrogen sources (NH_3 and N_2) are demonstrated, inducing crystallinity and dangling bonds in InON. The associated thin film transistor performances are exhibited.

As featured in:



See Jin-Seong Park *et al.*,
J. Mater. Chem. C, 2023, **11**, 14571.